EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	(semiconductor and power and substrate and voltage and sustain$3 and trench and column and diffus$3 and sidewall and adjacent and vertical$3 and fill$3 and junction).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 16:58
L2	6	(semiconductor and power and substrate and voltage and sustain$3 and trench and barrier and etch$3 and fill$3 and diffus$3 and overlap$4).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 17:00